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26. (New) The trench capacitor as recited in claim 23, wherein the crystalline nitride layer is between 2 and 6 atoms thick.

27. (New) The trench capacitor as recited in claim 23, wherein the crystalline nitride layer includes stoichiometric Si_3N_4 .

28. (New) The trench capacitor as recited in claim 23, wherein the electrodes includes a storage node and a buried plate.

29. (New) The trench capacitor as recited in claim 23, wherein the crystalline nitride layer provides a gate dielectric layer.

REMARKS

In view of the addition of new claims, it is respectfully submitted that no new matter has been added and that all of the claimed matter has support in the specification and drawings.

Claims 18-29 are now pending in the case. Claims 21-29 have been added.

In view of the foregoing amendments and remarks, it is respectfully submitted that all the claims now pending in the application are in condition for allowance. Early and favorable reconsideration of the case is respectfully requested.

Respectfully submitted,

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